

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Amit S. Kelkar et al. PATENT APPLICATION
Serial No.: 10/606,426 Group Art Unit: 2812
Filed: June 25, 2003 Examiner: A.G. Ghyka
Confirmation No.: 6317 Attorney Docket No.: ATM-247
For: METHOD OF FORMING PRE-METAL DIELECTRIC FILM
ON A SEMICONDUCTOR SUBSTRATE INCLUDING FIRST
LAYER OF UNDOPED OXIDE OF HIGH OZONE:TEOS
VOLUME RATIO AND SECOND LAYER OF LOW OZONE
DOPED BPSG

Amendment

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir or Madam:

In response to the Office action mailed on
03/09/2007, Applicant hereby submits the following amendment
in the above application.

The amendments set forth herein are provided solely
to clarify the invention as filed and set forth in the pending
claims in order to comply with applicable statutes and
regulations.

As the statutory period for reply to this Office
action expired June 9, 2007, Applicants request a one-month
extension of time in accordance with 37 C.F.R. § 1.36(a). The
appropriate fee set forth in § 1.17(a) is submitted with this
Amendment.

Amendments to the Claims begin on page 2 of this paper.

Remarks begin on page 7 of this paper.